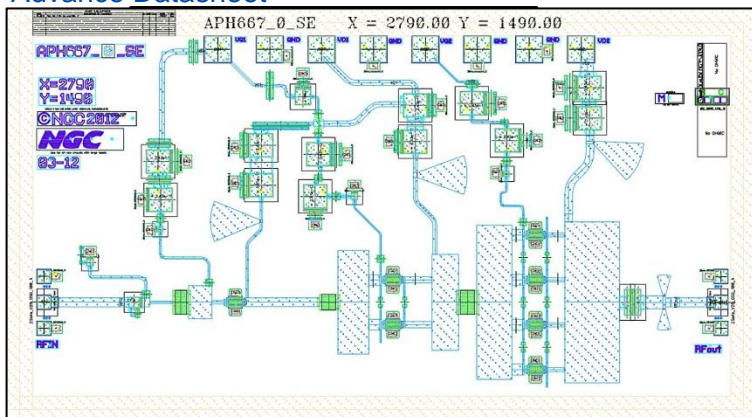


Advance Datasheet

Revision: October 2012

X=2800 μ m Y=1490 μ m (See NOTE)**Product Features**

- ◆ RF Frequency: 81 to 86 GHz
- ◆ Linear Gain: 14 dB typ.
- ◆ Psat: 23.5 dBm typ.
- ◆ Die Size: 4.17 sq. mm.
- ◆ 2 mil substrate
- ◆ DC Power: 4 VDC @ 305 mA

Performance Characteristics (Ta = 25°C)

Specification	Min	Typ	Max	Unit
Frequency	81		86	GHz
Linear Gain	15	18		dB
Input Return Loss	7	11		dB
Output Return Loss	8	12		dB
P1dB		TBD		dBm
Psat		23.5		dBm
Vd1=Vd1a, Vd2=Vd2a		4		V
Vg1=Vg1a		0		V
Vg2a=Vg2b		0		V
Id1+Id1a		135		mA
Id2+Id2a		180		mA

Applications

- ◆ FCC E-band Communication Systems @ 81-86 GHz Frequency Band
- ◆ Short Haul / High Capacity Links
- ◆ Enterprise Wireless LAN
- ◆ Wireless Fiber Replacement

Product Description

The APH669* is a Gallium Arsenide-based broadband, three-stage power device, designed for use in commercial digital radios and wireless LANs. It can be used as a Driver Amplifier as a companion to the APH667 or as a stand-alone amplifier.

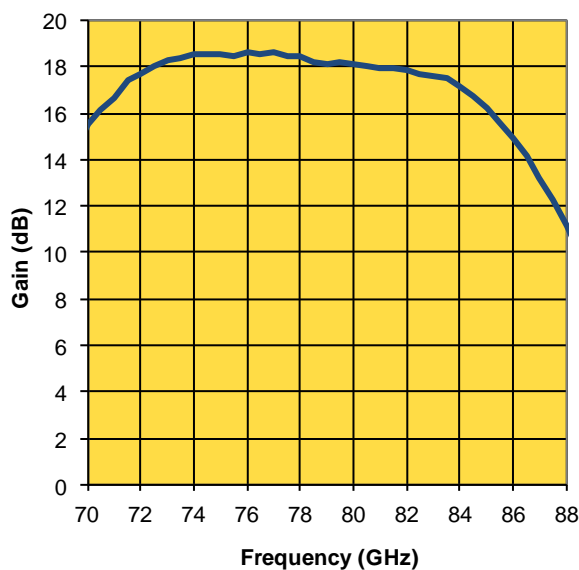
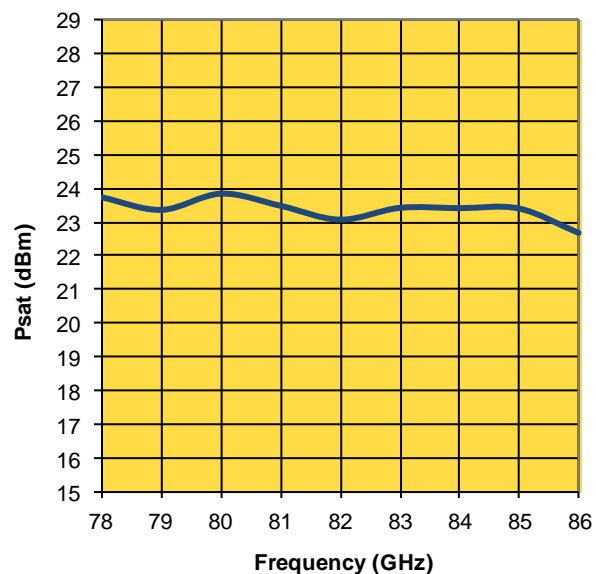
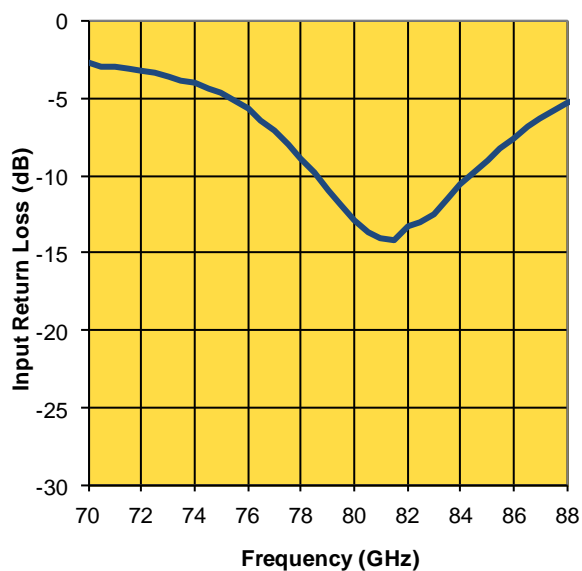
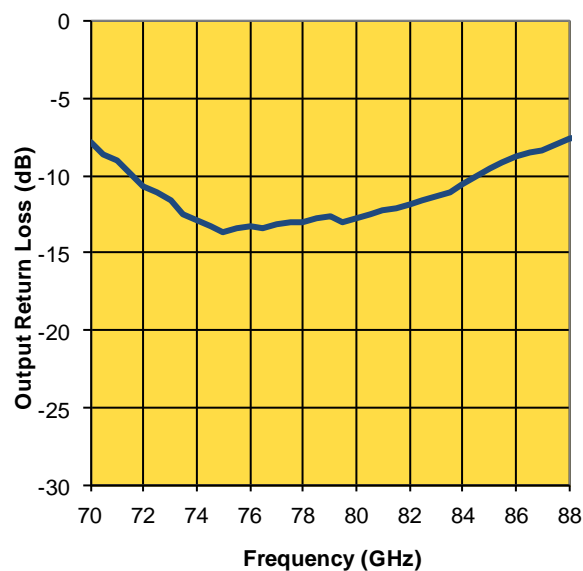
NOTE

Samples of the APH669 may have the product name "APH667_SE" and be slightly different in size (2790X1490)

Absolute Maximum Ratings (Ta = 25 C)

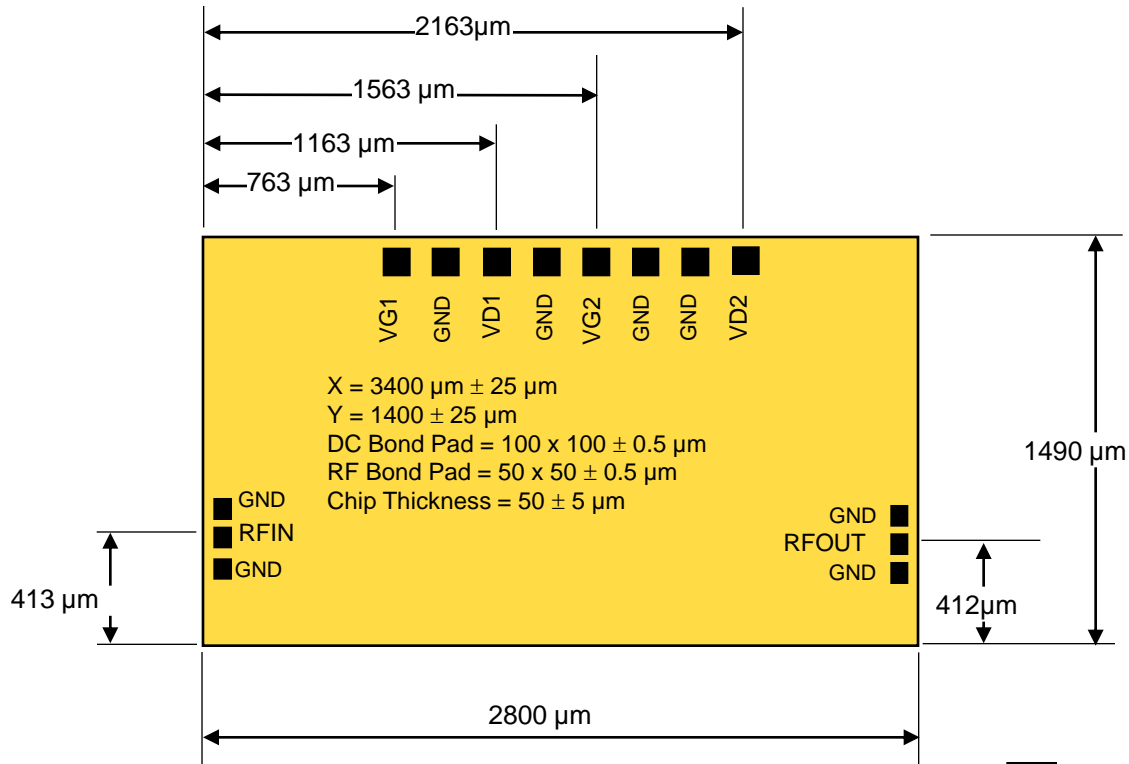
Parameter	Min	Max	Unit
Vd1=Vd1a, Vd2=Vd2a		4.5	V
Vg1=Vg1a	-0.8	0.3	V
Vg2a=Vg2b	-0.8	0.3	V
Id1+Id1a		150	mA
Id2+Id2a		200	mA
Input Drive Level		16	dBm
Assy. Temperature (60 seconds)		300	deg. C

Note: The data contained in this document is for information only. Northrop Grumman reserves the right to change without notice the specifications, designs, prices or conditions of sale, as they apply to this product. The product represented by this datasheet is subject to U.S. Export Law as contained in the Export Administration Regulations (EAR).

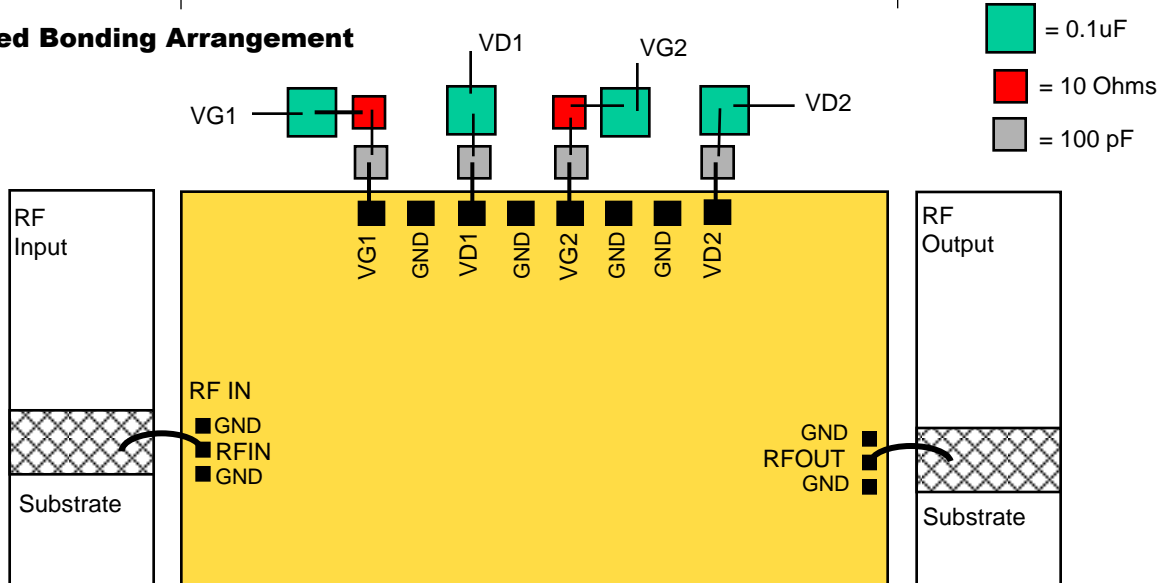
Measured (On-Wafer) Performance Characteristics (Typical Performance at 25°C)**V_d = 4V, I_{d1} = 135 mA, I_{d2} = 177 mA****Linear Gain Versus Frequency****Pulsed Power Output Power Versus Frequency****Input Return Loss Versus Frequency****Output Return Loss Versus Frequency**

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Die Size and Bond Pad Locations



Suggested Bonding Arrangement



Recommended Assembly Notes

1. Bypass caps should be 100 pF ceramic (single-layer) placed no further than 30 mils from the amplifier.
2. Best performance obtained from use of <10 mil (long) by 3 by 0.5 mil ribbons on input and output.

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